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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Examiner: Lee, Kyoung

Patent No.: 7,211,512

Group Art Unit: 2812

Lissue Date: May 1, 2007

Docket No: 303.672US1

Title: SELECTIVE ELECTROLESS-PLATED COPPER METALLIZATION

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

ATTN: CERTIFICATE OF CORRECTION BRANCH

Certificate

JUN 1 3 2007

of Correction

We are transmitting herewith the attached:

X Request for Certificate of Correction.
 X Certificate of Correction Form - PTO-1050 (in duplicate)

X Authorization to charge Deposit Account 19-0743 in the amount of \$100.00 to cover the Certificate of Correction fee.

 \underline{X} A return postcard.

Please charge any additional fees or credit overpayment to Deposit Account No. 19-0743

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

Customer No: 21186

Name: Timothy B. Clise

Reg. No.40,957 TBC/cmb

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner of Patents and Trademarks, P.O. Box 1450, Alexandria VA 22313-1450, on this _____ day of June 2007.

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Signature

Parent 7,211,512
PARENT AND TRADEMARK OFFICE

Patent No.: 7,211,512 Docket No: 303.672US1
Issue Date: May 1, 2007 Patentee: Kie Y. Ahn et al.

Customer No.: 21186 Confirmation No.: 8976

Title SELECTIVE ELECTROLESS-PLATED COPPER METALLIZATION

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ATTN: CERTIFICATE OF CORRECTION BRANCH

It is requested that a Certificate of Correction be issued correcting printing errors appearing in the above-identified United States patent. Two copies of the text of the Certificate in the suggested form are enclosed.

Pursuant to 1.20(a), The Commissioner is authorized to charge Deposit Account No. 19-0743 in the amount of \$100.00.

Issuance of the Certificate of Correction would neither expand nor contract the scope of the claims as properly allowed, and re-examination is not required.

The Examiner is authorized to charge any additional fees or credit overpayment to Deposit Account No.19-0743.

Respectfully Submitted

KIE Y. AHN ET AL.

06/11/2007 HDEMESS2 00000026 190743 7211512

01 FC:1811

100.00 DA

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A

P.O. Box 2938

Minneapolis, MN 55402

(612) 373-6990

Date .

Timothy B. Clise

Reg. No: 40,957

TBC/cmb

CERTIFICATE UNDER 37 CFR § 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, P.O. Box 1450 Alexandria, VA 22313-1450, on this ______ day of June 2007

2313-1430, on this ____ day of <u>June</u> 2007

Signatur

PATENT

(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO

: 7,211,512

Page (1) of 20

DATED

: May 1, 2007

INVENTOR(S)

: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the face page, in field (56), under "U.S. Patent Documents", in column 1, line 1, above "2,842,438 A 7/1958 Saarivirta et al. 75/153" insert

- - 1,254,987

1/1918 Cooper

1,976,375 10/1934 Smith, J. K. 2,244,608 6/1941 Cooper, H. S.

148/11.5 75/138 - -.

On the face page, in field (56), under "U.S. Patent Documents", in column 1, line 2, below "2,842,438 A 7/1958 Saarivirta et al. 75/153" insert

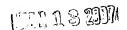
3,147,1°	10 9/196	34 Foerster	75/122.5
3,337,334	8/1967	Fenn et al.	75/150
3,506,438	4/1970	Krock et al.	75/208
3,548,915	10/1970	Richmond et al.	164/68
3,548,948	12/1970	Richmond et al.	164/68
3,687,737	8/1972	Krock et al.	148/2
3,832,456	8/1974	Kobetz et al.	423/645
3,932,226	1/1976	Klatskin et al.	204/16
3,954,570	6/1976	Shirk et al.	204/15
4,022,931	5/1977	Black et al.	427/91
4,029,377	6/1977	Guglielmi	339/19
4,065,330	12/1977	Masumoto et al.	148/31.55
4,101,855	7/1978	Drapeau	335/106
4,158,719		Frantz	428/567
4,213,818		Lemons et al.	438/719
4,233,066	11/1980	Sundin et al.	75/142
4,314,594	2/1982	Pfeifer et al.	148/108
4,386,116	5/1983	Nair et al.	427/99
4,389,429		Soclof	438/492
4,423,547	1/1984	Farrar et al.	29/571
4,561,173	12/1985	Te Velde	438/619

MAILING ADDRESS OF SENDER:

PATENT NO. _____7,211,512____

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A. P.O. BOX 2938 Minneapolis, MN $\,$ 55402

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PATENT NO

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Page (2) of 20

DATED

: May 1, 2007

INVENTOR(S)

: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the face page, in field (56), under "U.S. Patent Documents", in column 1, line 4, below "4.565,157 A 1/1986 Brors et al." insert

-- 4.574.095 3/1986 Blaum et al.

427/53.1

4,670,297 6/1987 Lee et al.

427/91

4,709,359 11/1987 Loftin

367/155 - -.

On the face page, in field (56), under "U.S. Patent Documents", in column 1, line 5, below "4,762,728 A 8/1988 Keyser et al. 427/38" insert

--4,788,082 11/1988 Schmitt

4.824.544 4/1989 Mikalesen et al. - -.

On the face page, in field (56), under "U.S. Patent Documents", in column 1, line 6, below "4,847,111 A 7/1989 Chow et al. 427/38" insert

- - 4,857,481 8/1989 Tam et al.

437/182

4,931,410 6/1990 Tokunaga et al.

437/189

4,933,743 6/1990 Thomas et al. - -,

On the face page, in field (56), under "U.S. Patent Documents", in column 1, line 8, below "4,962,058 A 10/1990 Cronin et al. 437/187" insert

-- 4,996,584 2/1991 Young et al.

357/71

5,019,531 5/1991 Awaya et al.

437/180 - -.

On the face page, in field (56), under "U.S. Patent Documents", in column 1, line 10, below "5,043,299 A 8/1991 Chang et al." insert

--5,045,635 9/1991 Kaplo et al.

174/35 GC

5,071,518 12/1991 Pan - -.

On the face page, in field (56), under "U.S. Patent Documents", in column 1, line 11, below "5.084.412 A 1/1992 Nakasaki 437/189" insert

--5,100,499 3/1992 Douglas

156/635 - -.

MAILING ADDRESS OF SENDER:

PATENT NO. 7,211,512

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A. P.O. BOX 2938 Minneapolis, MN 55402

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UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

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Page (3) of 20

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INVENTOR(S)

: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the face page, in field (56), under "U.S. Patent Documents", in column 1, line 12, below "5,130,274 A 7/1992 Harper et al. 437/195" insert

-- 5,148,260 9/1992 Inoue et al.

357/67

5,149,615 9/1992 Chakravorty et al.

430/313 - -.

On the face page, in field (56), under "U.S. Patent Documents", in column 1, line 15, below "5,180,687 A 1/1993 Mikoshiba et al." insert

-- 5,227,658 7/1993 Beyer et al.

257/522

5,231,036 7/1993 Miyauchi et al. - -.

On the face page, in field (56), under "U.S. Patent Documents", in column 1, line 16, below "5 231 056 A 7/1993 Sandhu

3,231,030	A II 1990 S	oanulu 43//	200 HISELL
5,232,86	6 8/1993	Beyer et al.	437/62
5,240,878	8/1993	Fitzsimmons et a	l. 437/187
5,243,222	9/1993	Harper et al.	257/774
5,256,205	10/1993	Schmitt III et al.	118/723
5,268,315	12/1993	Prasad et al.	437/31
5,308,440	5/1994	Chino et al.	156/664
5,324,683	6/1994	Fitch et al.	437/65
5,324,684	6/1994	Kermani et al.	437/95
5,334,356	8/1994	Baldwin et al.	422/133
5,336,914	8/1994	Andoh	257/368

On the face page, in field (56), under "U.S. Patent Documents", in column 1, line 17, below "5,348,811 A 9/1994 Nagao et al." insert

- - 5,354,712 10/1994 Ho et al. 437/195

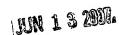
5,356,672 10/1994 Schmitt III et al. 427/446 - -.

MAILING ADDRESS OF SENDER:

PATENT NO. ______7,211,512__

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A. P.O. BOX 2938 Minneapolis, MN 55402

No. of additional copies



PATENT NO : 7.211.512 Page (4) of 20

DATED

: May 1, 2007

INVENTOR(S)

: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the face page, in field (56), under "U.S. Patent Documents", in column 2, line 1, above "5,413,687 A 5/1995 Barton et al. 204/192.14" insert

12/1994 Tada - - 5,374,849

5.384.284 1/1995 Doan et al. 437/190 Cunningham et al. 257/467 5,399,897 3/1995

3/1995 Abt et al. 5,401,680

5,408,742 4/1995 Zaidel et al. 29/846 - -.

On the face page, in field (56), under "U.S. Patent Documents", in column 2, line 2, below "5,413,687 A 5/1995 Barton et al. 204/192.14" insert

-- 5,413,962 5/1995 Lur et al. 437/195 420/473 5,424,030 6/1995 Takahashi 5,426,330 6/1995 Joshi et al. 257/752 5,442,237 8/1995 Hughes et al. 257/759 5,444,015 8/1995 Aitken et al. 437/182 - -.

On the face page, in field (74), in "Attorney, Agent, or Firm", in column 2, line 1, delete "Lunberg" and insert - - Lundberg - -, therefor.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 2, below "5,447,887 A 9/1995 Filipiak et al. 437/200" insert

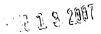
•, , • • .		.p.a., 0. a., 10., 120	
5,457,34	4 10/1995	Bartelink	257/737
5,470,789	11/1995	Misawa	437/190
5,470,801	11/1995	Kapoor et al.	437/238
5,476,817	12/1995	Numata	437/195
5,485,037	1/1996	Marrs.	257/712
5,495,667	* 5/1996	Earnworth et al.	29
5,506,449	41996	Nakano et al.	257/758
5,510,645	4/1996	Fitch et al.	257/522
5,529,956	61996	Morishita	437/195
5,534,731	7/1996	Cheung	257/759
5,538,922	7/1996	Cooper et al.	437/195
5,539,060	7/1996	Tsunogae et al.	525/338
5.539.227	7/1996	Nakano	257/276

MAILING ADDRESS OF SENDER:

PATENT NO. 7,211,512

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PATENT NO

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Page (5) of 20

DATED

: May 1, 2007

INVENTOR(S)

: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 3, below "5,572,072 A 11/1996 Lee" insert - -

5,578,146 11/1996

Grant et al. 148/437 - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 5, below "5,609,721 A 3/1997 Tsukune et al. 156/646.1" insert

- - 5.625.232

4/1997

Numata et al

5,633,200

5,635,253

5/1997

6/1997

Hu Canaper

427/437 - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 6, below "5,654,245 A 8/1997 Allen 438/629" insert

205/87

- - 5,662,788 5,667,600

9/1997 Sandhu et al. 9/1997 Grensing et al

148/437 - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 7, below "5,670,420 A 9/1997 Choi 437/189" insert

- - 5,674,787 10/1997 Zhao et al.

437/230

5.675,187 10/1997 Numata et al.

257/758

5,679,608 10/1997

437/195

5,681,441 10/1997

Cheung et al.

5,693,563 12/1997

Svendsen et al.

205/114

5,695,810 12/1997

Teona

427/96

Dubin et al. 5,705,425 1/1998 Miura et al. 437/182 - -.

"5,719,089 A 2/1998 Cherng et al.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 8, below 438/637" insert

2/1998 Suehiro et al. - - 5,719,410

257/77

5,719,447

2/1998 Gardner

5,725,689 5,739,579

3/1998 Nishida et al. 4/1998 Chiang et al.

148/320 257/635 - -.

MAILING ADDRESS OF SENDER:

PATENT NO. _____7,211,512___

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A. P.O. BOX 2938 Minneapolis, MN 55402

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PATENT NO

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Page (6) of 20

DATED

: May 1, 2007

INVENTOR(S)

: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 9, below

"5,763,953 A 6/1998 Iljima et al. 257/762" insert 438/645 - - 5,780,358 7/1998 Zhou

5,785,570 7/1998 445/52 Bruni 5,789,264 8/1998 Chung

5,792,522 81998 Jin et al. 427/575 5,792,706 8/1998 Michael et al. 438/626 5,801,098 9/1998 Fiordalice et al. 438/653 5.814.557 9/1998 Venkataraman et al. 438/622 5,821,168 10/1998 Jain 438/692 - - .

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 10, below "5,824,599 A 10/1998 Schacham-Diamand et al. 438/678" insert

- - 5,840,625 11/1998 Feldner

5,852,871 12/1998 Khandros 29/843 5,858,877 1/1999 Dennison et al. 438/700 5.880.018 03/1999 438/619 - -. Boeck

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 11, below "5,891,797 A 4/1999 Farrar 438/619" insert

- - 5,880,018 4/1999 Havemann et al. 438/674 5,893,752 4/1999 Zhang et al. 438/687 - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 12, below "5,895,740 A 4/1999 Chien et al. 430/313" insert

- - 5,897,370 4/1999 Joshi et al. 438/632

5,899,740 5/1999 Kwon

5,900, 668 5/1999 Wollesen

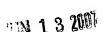
257/522 - -.

MAILING ADDRESS OF SENDER:

PATENT NO. _____7,211,512___

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A. P.O. BOX 2938 Minneapolis, MN 55402

Atty Docket No: 303.672US1



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UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO

: 7,211,512

Page (7) of 20

DATED

: May 1, 2007

INVENTOR(S)

: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 13, below

"5,907,772 A	5/1999	lwasaki 438/2	53" insert
5,911,113	6/1999	Yao et al.	438/649
5,913,147	6/1999	Dubin et al.	438/687
5,925,930	7/1999	Farnworth et al.	257/737
5,930,596	7/1999	Klose et al.	438/98
5,930,669	7/1999	Uzoh	438/627
5,932,928	8/1999	Clampitt	257/758
5,933,758	8/1999	Jain	438/687
5,937,320 A	* 8/1999	Andricacos et al.	438/614
5.940.733	8/1999	Beinglass et al.	438/655

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 15, below "5,962,923 A 10/1999 Xu et al. 257/774"insert

- - 5,968,327 10/1999 Kobayashi et al.

5,968,333 10/1999 Nogami et al. 205/184 5,969,422 10/1999 Ting et al. 257/762 - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 16, below "5,972,179 A 10/1999 Chittipeddi et al. 204/192.17" insert

- - 5,972,804 10/1999 Tobin et al. 438/786 5,976,710 11/1999 Sachdev et al. 428/620

5,981,350 11/1999 Geusic et al. 438/386 5,985,759 11/1999 Kim et al. 438/653 - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 17, below "5,989,623 A 11/1999 Chen et al. 427/97" insert

- - 5,994,776

11/1999

Fang et al.

257/758 - -.

MAILING ADDRESS OF SENDER:

PATENT NO. _____7,211,512____

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A. P.O. BOX 2938 Minneapolis, MN 55402

No. of additional copies

Atty Docket No: 303.672US1

(132M)

PATENT NO

: 7,211,512

Page (8) of 20

DATED

: May 1, 2007

INVENTOR(S)

: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 18, below "6,001,736 A 12/1999 Kondo et al." insert

Abraham

438/714

- - 6.004.884 6,008,117

12/1999 12/1999

Hong et al.

438/629 - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 19, below 1/2000 Kholodenko et al. 118/719" insert "6,015,465 A

- - 6.015.738

1/2000

Levy et al.

438/275 - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 20, below

1/2000 Ting et al." insert "6,017,820 A

- - 6,022,802

2/2000 Jang

438/656

6,028,362

2/2000 Omura

6,025,261 6,030,877 2//2000 Farrar et al. 2/2000 Lee et al.

438/619 438/381

6,030,895

2/2000 Joshi et al.

6,037,248 6,054,172 3/2000 Ahn 4/2000 Robinson et al.

438/619 427/97

6,057,226

5//2000 Wong

438/623

6,065,424 6,069,068

6,126,989

5/2000 Shachem-Diamand et al. 118/696 5/2000 Rathore et al.

438/628 - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 21, below

"6,071,810 A 6/2000 Wada et al. 438/635" insert - - 6,075,278 6/2000 Farrar 257/522

6.075,287 6/2000 Ingraham et al. 6,091,136 7/2000

6,091,475 7/2000 6,100,193

Jiang et al. Ogino et al. 257/676 349/149

8/2000 Suehiro et al. 8/2000 Matsumoto et al.

10/2000

438/685

Robinson et al. 427/97 - -.

6,103,320 6,120,641 10/2000 6,121,126 9/2000

Stevens et al. 456/345.22 Ahn et al.

438/602

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INVENTOR(S)

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It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 25, below

"6.140.234 A 10/2000 Uzoh et al." insert

10/2000

Lee et al.

528/196

- - 6,140,456 6,143,641

11/2000

Kitch

438/618

11/2000

6,143,655

Forbes et al. - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 26, below "6,143,646 A 11/2000 Wetzel et al. 438/637" insert

- - 6,143,671

11/2000 Sugai

6,150,214

11/2000 Kaeriyama

6,150,261

11/2000 Hsu et al.

438/640 - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 28, below "6,153,507 A 11/2000 Mikagi et al. 438/618" insert

- - 6,159,769

12/2000 Farnworth et al. 438/108

6,159,842

Chang et al. 438/622 12/2000

6,169,024

1/2001 Hussein - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 29, below "6,171,661 B1 1/2000 Zheng et al. 427/535" insert

- - 6,174,804

1/2001 Hsu - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 31, below 2/2001 Reynolds et al. 118/719" insert "6,183,564 B1

- - 6,187,656

2/2001 Lu et al.

438/592 - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 33, below "6,197,688 B1 3/2001 Simpson 4380/678" insert

- - 6,197,181

* 3/2001

Chen

205/123

6,204,065

3/2001

Ochiai

436/66 - -.

MAILING ADDRESS OF SENDER:

PATENT NO. _____7,211,512____

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Page (10) of 20

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: May 1, 2007

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: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 34, below "6,207,222 B1 3/2001 Chen et al. 427/678" insert

5/2001 Buynoski et al. 438/622

- - 6,207,553

3/2001 Singhbi et al. 438/648

6,207,558 6,208,016

3/2001 Farrar 257/643 - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 35, below "6 211 073 B1 4/2001 Ahn et al 438/653" insert

0,211,013 01	4/2001 AII	11 GLai. 400	7000 IIISCIL
6,211,049	4/2001	Farrar	438/597
6,211,561	4/2001	Zhao	257/522
6,214,719	4/2001	Nag	438/619
6,215,186	4/2001	Konecni et a	al.
6,218,282	4/2001	Buynoski	438/619
6.221.763	4/2001	Gilton	438/643

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 36, below "6 232 219 B1 5/2001 Blalock et al. 438/637" insert

0,232,219 01	3/2001 61	alock et al.	430/03/	1561
6,245,658	6/2001	Buynoski	438/619	ı
6,245,662 B1	* 6/2001	Naik et al.	438/622	
6.246.118	6/2001	Buvnoski	257/758	

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 38, below "6,251,781 B1 6/2001 Zhou et al. 438/637" insert

- - 6,258,707 7/2001 Uzoh - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 39, below "6,265,311 B1 7/2001 Hautala et al. 438/680" insert

- - 6.265.811

7/2001

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6,268,276

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SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.

Bang

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PATENT NO

: 7,211,512

Page (11) of 20

DATED

: May 1, 2007

INVENTOR(S)

: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 40, below

"6,271,592 B1	8/2001 K	ım et ai.	25///51" insert
6,277,263	8/2001	Chen	205/182
6,281,585	8/2001	Bothra	257/758
6,284,656	9/2001	Farrar	438/687
6,287,954	9/2001	Ashley	438/622
6,288,442	9/2001	Farrar	257/678
6,288,447	9/2001	Amishiro	et al.
6,288,905	9/2001	Chung	361/771
6,290,833	9/2001	Chen	205/182

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 42, below

"6,303,505 B1 10/2001 Ngo et al." insert - - 6,323,543 11/2001 Jiang et al. 257/676 6,323,553 11/2001 Hsu et al. 257/751 6,326,303 12/2001 Robinson et al. 38/678 6.329.279 12/2001 Lee 438/619 6,342,448 1/2002 Lin et al. 438/687 6,358,842 3/2002 Zhou et al. 438/633 6,358,849 3/2002 Havemann et al. 438/689 6,359,328 3/002 Dunbin 257/62 - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 43, below "6,365,511 B1 4/2002 Kizilyalli et al." insert

- - 6,368,954 4/2002 Lopatin et al. 438/622 6,368,966 4/2002 Krishnamoorthy 438/687 - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 44, below "6,372,622 B1 * 4/2002 Tan et al."insert

- - 6,376,370 4/2002 Farrar 438/678 6,383,920 5/2002 Wang et al. 438/639 - -.

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PATENT NO : 7,211,512 Page (12) of 20

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: May 1, 2007

INVENTOR(S)

: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 45, below "6,387,542 B1 * 5/2002 Kozlov et al."insert

- - 6.399.489

6/2002 M'Saad et al. 438/680 - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 46, below "6,403,481 B1 * 6/2002 Matsuda et al." insert

0,400,401 B1 0/2002 Matsada Ct al.	IIIOCIT
6,403,481 6/2002 Matsuda et al.	438/687
6,417,094 7/2002 Zhao et al.	
6,428,673 8/2002 Ritzdorf et al.	205/84
6,429,120 8/2002 Ahn et al.	438/635
6,486,533 11/2002 Krishnamoorthy et al.	257/586
6,492,266 12/2002 Ngo et al.	
6,508,920 1/2003 Ritzdorf et al.	204/194
6,518,198 2/2003 Klein	438/758
6,552,432 4/2003 Farrar	257/751
6,563,219 5/2003 Ireland et al.	257/758
6,565,729 5/2003 Chen et al.	205/82
6,589,863 7/2003 Usami	
6,614,099 9/2003 Farrar	257/643
6,632,345 10/2003 Chen	205/182
6,638,410 10/2003 Chen et al.	205/182
6,664,197 12/2003 Stevens et al.	438/754
6,743,716 6/2004 Farrar	438/652
6,756,298 6/2004 Ahn et al.	438/635
2001/0002333 5/2001 Huang et al.	438/637
2001/0054771 12/2001 Wark et al.	257/786
2002/0014646 2/2002 Tsu et al.	257/296
2002/0028552 3/2002 Lee et al.	438/243
2002/0096768 7/2002 Joshi	257/750
2002/0109233 8/2002 Farrar	257/762
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2003/0034560 A1 2/2003 Matsuse et a	al.
2004/0206308 A1 10/2004 Ahn et al.	

2/2005 Ahn et al. - -.

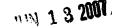
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PATENT NO

: 7,211,512

Page (13) of 20

DATED

: May 1, 2007

INVENTOR(S)

: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On page 3, in field (56), under "Other Publications", in column 1, line 37, delete "electrless" and insert - - electroless - -, therefor.

On page 3, in field (56), under "Other Publications", in column 1, line 37, delete "Si02" and insert - - SiO_2 - -, therefor.

On page 3, in field (56), under "Other Publications", in column 1, line 43, delete "on" and insert - - of - -, therefor.

On page 3, in field (56), under "Other Publications", in column 2, line 22, delete "mangetron" and insert - - magnetron - -, therefor.

On page 3, in field (56), under "Other Publications", in column 2, line 52, delete "SiO2" and insert - - SiO₂ - -, therefor.

On page 3, in field (56), under "Other Publications", in column 2, line 64, below "Thin Solid Films, 318, pp. 234-238, (1998)." insert

- - Abe, K., et al., "Sub-half Micron Copper Interconnects Using Reflow of Sputtered Copper Films", VLSI Multilevel Interconnection Conference, (June 25-27, 1995),308-311.

AMERICAN SOCIETY FOR METALS Metals Handbook, 8th Edition. Vol. 8, Metals Park, Ohio, (1973), 300-302.

AMERICAN SOCIETY FOR METALS, Metals Handbook, Ninth Edition. Vol. 2, Properties and Selection: Nonferrous Alloys and Pure Metals, ASM Handbook Committee, (eds.), American Society for Metals, Metals Park, OH,(1989),157, 395.AMERICAN SOCIETY FOR METALS, "Phase Diagrams", Metals Handbook, 10th Ed. Vol. 3, Metals Park, Ohio. (1992). Anonymo. "Formation of Conductors at Variable Depths - Using Differential Photomask, Projecting Images into Insulator by Reactive Ion Etching, Selectively Filling Images with Conductor", Research Disclosure, Disclosure No. RD 291015, Abstract, (July 10, 1988), 1 page.

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Page (14) of 20

DATED

: May 1, 2007

INVENTOR(S)

: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Chang, J. Y. C., et al., "Large Suspended Inductors on Silicon and their use in a 2-urn CMOS RF Amplifier", IEEE Electron Device Letters. 14(5), (May 1993),246-248. Craig, J. D., "Polymide Coatings", Packaging. Electronic Materials Handbook, Vol. 1. ASM International Handbook Committee (eds.), ASM International, Materials Park, OH,(1989),767-772.

DOW COMPANY, "SILK' D Semiconductor Dielectric Resin", http://www.dow.com/silk/odf/618 00317.pdf, (Unknown),2 pages.

DOW COMPANY, "SILK' J Semiconductor Dielectric Resin", http://www.dow.com/silk/ a df/618-00316.4df (unknown),2 pages.

Dudzinski, N., et al., "The Youngs Modulus of Some Aluminim Alloys", J. Institute of Metals, Vol. LXXIV, (1947-48),291-314.

Ernst, et al., "Growth Model for Metal Films on Oxide Surface: Cu on ZnO(0001)-O"", Physical Review B, 47, (May 15, 1993),13782-13796.

Fleming, J. G., et al., "Use Of Air Gap Structures To Lower Level Intralevel Capacitance", Proceedings of the 1997 Dielectrics for ULSI Multi-level Interconnect Conference, (1997), 140. Grill, A., et al., "Low dielectric constant films prepared by plasma-enhanced chemical vapor deposition from tetramethvisilane", Journal of Applied Physics, 85(6), (1999),3314-3318. Hirao, S., et al., "A Novel Copper Reflow Process Using Dual Wetting Layers", 1997 Symposium on VLSI Technology, Digest of Technical Papers, (1997), 57-58. Izaki, M., et al., "Characterization of Transparent Zinc Oxide Films Prepared by Electrochemical Reaction", Journal of the Electrochemical Society, 144. (June 1997),1949-

Jayaraj, K., et al., "Low Dielectric Constant Microcellular Foams", Proceedings from the Seventh Meeting of the DuPont Symposium on Polymides in Microelectrics September 1996 ,474-501.

Jin, C., et al., "Porous Xerogel Films as Ultra-low Permittivity Dielectrics for ULSI Interconnect Applications", Conference Proceedings ULSI XII -1997. Materials Research Society (1997),463-469.

Kang, H. K., et al., "Grain Structure and Electromigration Properties of CVD CU Metallization" Proceedings of the 10th International VLSI Multilevel Interconnection Conference June 8-9, 1993 .223-229.

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: 7.211.512

Page (15) of 20

DATED

: May 1, 2007

INVENTOR(S)

: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Kirk, Raymond E., Kirk-Othmer Concise Encyclopedia of Chemical Technology, Grayson, M., (ed.), John Wiley & Sons, Inc., New York, NY,(1985),433-435, 926-938.

Martin, Steven J., "The Invention and Development of a Low-Dielectric Constant Polymer for the Fabrication of Integrated Circuit Interconnect", Seminar - Department of Chemical Engineering - North Carolina State University, (April 9, 2001),1 page.

MIN, J., "Metal-organic atomic-layer deposition of titanium-silicon-nitride films", Applied Physics Letters, 75(11), (1999),1521-1523.

Miyake, T. et al., "Atomic Hydrogen Enhanced Reflow of Copper" Applied, Physics Letters. 70(10), (1997),1239-1241.

Palleau, J., et al., "Refractory Metal Encapsulation in Copper Wiring", Advanced Metallization for Devices and Circuits-Science, Technology and Manufacturability, Materials Research Society Symposium Proceedings, 337, (April 1994),225 – 231.

Park, C. W., et al., "Activation Energy for Electromigration in Cu Films", Applied Physics Letters, 59(2), (July 6, 1991),175-177.

Quan, Y. C., et al., "Polymer-like Organic Thin Films Deposited by Plasma Enhanced Chemical Vapor Deposition Using the Para-xylene Precursor as Low Dielectric Constant Interlayer Dielectrics for Multilevel Metallization", Japanese Journal of Applied Physics. Vol. 38. Part1, No. 3A 1999, 1356-1358.

Ramos, T, et al., "Nanoporous Silica for Dielectric Constant Less Than 2", Conference Proceedings ULSI XII - 1997 Materials Research Society,(1997),455-461.

Rossnagel, S. M., "Magnetron Sputter Deposition of Interconnect Applications", Conference Proceedings, ULSI XI, (1996),227-232.

Shacham-Diamand, Y., "100 nm Wide Copper Lines Made by Selective Electroless Deposition", Journal of Micromechanics and Microengineering. 1, (March 1991),66-72. Shieh, B., et al., "Air-Gap Formation During IMD Deposition to Lower Interconnect Capacitance", IEEE Electron Device Letters, 19(1), (1998),16-18.

Singer, Ferdinand L., "Strength of Materials", Harper & Brothers. New York, (1951),229-32. Srivatsa, A. R., et al., "Jet Vapor Deposition: an Alternative to Electrodeposition", Surface Engineering. 11, (1995),75-77.

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PATENT NO

: 7.211.512

Page (16) of 20

DATED

: May 1, 2007

INVENTOR(S)

: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Tao, J., et al., "Electromigration Characteristics of Copper Interconnects", IEEE Electron Devices Letters, 14(5), (May 1993),249-251.

Ting, C. H., "Methods and Needs for Low K Material Research", Materials Research Society Symposium Proceedings. Volume 381, Low-Dielectric Constant Materials -- Synthesis and Applications in Microelectronics, Lu, T.M., et al., (eds.), San Francisco, CA,(April 17-19,1995) 3-17.

Uchida, Y., et al., "A Fluorinated Organic-Silica Film with Extremely Low Dielectric Constant". Japanese Journal of Applied Physics. Vol. 38 Part1 No. 4B, (April 1999),2368-2372. Ueda, T., et al., "A novel Air Gap Integration Scheme for Multi-level Interconnects using Selfaligned Via Plugs" Symposium on VLSI Technology Digest of Technical Papers (1998), 46-47.

Wang, X. W., et al., "Highly Reliable Silicon Nitride Thin Films Made by Jet Vapor Deposition" Japanese Journal of Applied Physics. Vol. 34, Putt No. 2B, (February 1995),955-958. Wolf, S., et al., Silicon Processing for the VLSI Era. Vol. 1 - Process Technology, Lattice Press, Sunset Beach, CA,(1986),514-538.

Wolf, S., "Chapter 4: Multilevel-Interconnect Technology for VLSI and ULSI", Silicon Processing for the VLSI Era, Vol. 2 Process Integration, Lattice Press, Sunset Beach, CA,(1990),176-297.

Zhang, F, et al., "Nanoglass/sup TM/ E copper damascene processing for etch, clean, and CMP", Proceedings of the IEEE 2001 International Interconnect Technology Conference, (2001),57-9.

AMERICAN SOCIETY FOR METALS, "Properties and Selection: Nonferrous Alloys and Pure Metals", Metals Handbook. 9th ed.. vol. 2, Metals Park, Ohio,(1979), Table of Contents. Van Horn, K. R., "Aluminum Vol. III Fabrication and Finishing", American Society for Metals, Metals Park, OH,(1967),468.

Murarka, S. P., et al., Topper Metallization for ULSI and Beyond' Critical Reviews in Solid State and Materials Sciences 20 2 1995, 87-124.

Bai, G., "Copper Interconnection Deposition Techniques and Integration", 1996 Symposium on VLSI Technoloay, Digest of Technical Papers, (1996), pp. 48-49.

Bhansali, S., et al., "Selective seeding of copper films on polyimide-patterned silicon substrate, using ion implantation", Sensors and Actuators A: Physical, 52 1 March 1996, 126-131. - -.

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PATENT NO

: 7,211,512

Page (17) of 20

DATED

: May 1, 2007

INVENTOR(S)

: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 3, line 66, after "invention" delete "." and insert --; --, therefor.

In column 4, line 22, delete "unhoped" and insert - - undoped - -, therefor.

In column 11, line 52, delete "copending" and insert - - co-pending - -, therefor.

In column 13, line 54, in Claim 1, before "seed" insert - - discontinuous - -.

In column 13, line 56, in Claim 1, after "on" delete "the substrate" and insert - - a semiconductor substrate, wherein individual elements of the discontinuous seed layer are substantially isolated from each other - -, therefor.

In column 13, line 63, in Claim 1, after "layer" insert - - and exposed portions of the seed layer - -.

In column 14, line 9, in Claim 5, before "seed" insert - - discontinuous - -.

In column 14, line 10, in Claim 5, delete "(Cu)having" and insert - - (Cu) having - -, therefor.

In column 14, line 10, in Claim 5, before "discontinuous" delete "a".

In column 14, lines 10-11, in Claim 5, delete "island structure on the" and insert - - islands on a semiconductor - -, therefor.

In column 14, line 12, in Claim 5, delete "technique;" and insert - - technique, wherein the discontinuous islands are substantially electrically isolated from each other; - -, therefor.

In column 14, line 16, in Claim 5, after "layer;" insert - - and - -.

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UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO

: 7,211,512

Page (18) of 20

DATED

: May 1, 2007

INVENTOR(S)

: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 14, lines 20–21, in Claim 6, delete "having a discontinuous island structure includes a discontinuous island structure" and insert - - includes discontinuous islands - -, therefor.

In column 14, line 25, in Claim 7, delete "vias, wherein the number of copper vias form" and insert - - structures, wherein copper structures are formed - -, therefor.

In column 14, line 28, in Claim 8, delete "vias" and insert - - structures - -, therefor.

In column 14, line 35, in Claim 10, after "first" insert - - discontinuous - -.

In column 14, line 36, in Claim 10, delete "substrate;" and insert - - semiconductor substrate, wherein individual elements of the first discontinuous seed layer are substantially electrically isolated from each other; - -, therefor.

In column 14, line 40, in Claim 10, after "of" delete "or".

In column 14, line 45, in Claim 10, after "second" insert - - discontinuous - -.

In column 14, line 46, in Claim 10, after "(Pd)" insert - - or - -.

In column 14, line 65, in Claim 13, after "first" delete "number of".

In column 14, line 66, in Claim 13, delete "form" and insert - - are formed - -, therefor.

In column 15, line 14, in Claim 17, before "seed" insert - - discontinuous - -.

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UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO

: 7,211,512

Page (19) of 20

DATED

: May 1, 2007

INVENTOR(S)

: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 15, line 14, In Claim 17, delete "substrate" and insert - - semiconductor substrate, wherein individual elements of the first discontinuous seed layer are substantially electrically isolated from each other - -, therefor.

In column 15, line 19, in Claim 17, delete "plating;" and insert - - plating to a top surface of the first photoresist layer; - -, therefor.

In column 15, line 20, in Claim 17, after "second" insert - - discontinuous - -.

In column 15, line 28, in Claim 17, after "third" insert - - discontinuous - -.

In column 15, line 38, in Claim 18, after "fourth" insert - - discontinuous - -.

In column 16, line 3, in Claim 25, after "first" insert - - discontinuous - -.

In column 16, line 4, in Claim 25, before "substrate" insert - - semiconductor - -.

In column 16, line 5, in Claim 25, delete "process;" and insert - - process, wherein individual elements of the first discontinuous seed layer are substantially electrically isolated from each other; - -, therefor.

In column 16, line 11, in Claim 25, after "plating" insert - - to a top surface of the first photoresist layer - -.

In column 16, line 12, in Claim 25, after "second" insert - - discontinuous - -.

In column 16, line 19, in Claim 25, after "third" insert - - discontinuous - -.

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: 7,211,512

Page (20) of 20

DATED

: May 1, 2007

INVENTOR(S)

: Ahn et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 16, line 50, in Claim 31, after "first" insert - - discontinuous - -.

In column 16, line 51, in Claim 31, delete "substrate;" and insert - - semiconductor substrate, wherein individual elements of the first discontinuous seed layer are substantially electrically isolated from each other; - -, therefor.

In column 16, line 57, in Claim 31, after "second" insert - - discontinuous - -.

In column 16, line 65, in Claim 31, after "third" insert - - discontinuous - -.

In column 17, line 3, in Claim 31, after "layer;" delete "and".

In column 17, line 6, in Claim 31, after "fourth" insert - - discontinuous - -.

In column 18, line 11, in Claim 37, delete "wherein the further includes" and insert - - further including - -, therefor.

In column 18, line 14, in Claim 37, after "and" insert - - on - -.

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